JMSLPD-1000-V2.00

1mm InGaAs PIN Photodiode

FEATURES:

- High Responsivity at 0.9um-1.7um
- Highly Reliable Planar Device
- Low Leakage Current
- High Shunt Resistance
- Wide Dynamic Range
- Responsivity (s) 0.6um-1.7um

APPLICATIONS:

- Power Monitoring
- Spectral Analysis
- Covert IR Sensing
- Light Detection and Ranging
- Remote Temperature Sensors
- Humidity Detection
- Gas Leak Detection

SPECIFICATIONS (T_a=25°C) :

Electro-Optical Characteristics (@Ta=25℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Responsivity	**R**	Vr=5V; λ=1310nm	0.80	0.90	-	A/W
Dark Current	**Id**	Vr=5V	-	2	10	nA
Breakdown Voltage	**Vb**	Ir=10uA	20	35	-	V
Capacitance	**C**	Vr=0V; f=1MHz		100	200	pF

Absolute maximum ratings:

Parameters	Symbol	Min	Max	Unit	Conditions
Storage Temperature	Tstg	-40	100	℃	
Operating Temperature	Top	-40	85	℃	
Reverse Current	Ir	-	2	mA	
Reverse Voltage	Vrd	-	20	V	
Forward Current	Ifd	-	10	mA	

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MECHANICAL DRAWING:

Structure

InGaAs / InP PIN Chip

P-electrode (anode) : Gold 1.0um minimum.

N-electrode (cathode) : Gold

Dimension

Chip Length : 1380 ± 20um

Chip Width : 1380 ± 20um

Thickness : 200 ± 30um

Active Area : 1000μm in diameter

Unit: um